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Substitute for form 1449A/PTO

(use as many sheets as necessary)

Sheet

1

of

3

Complete if Known

Application Number:

10/602,436

Filing Date:

06-23-03

First Named Inventor

Jong-Jan Lee

Art Unit

280

Examiner Name:

44. 40

Attorney Docket Number

SLA0733

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code (If known)	MM-DD-YYYY		
✓		US- 6,413,802 B1	07-02-2002	Hu et al.	
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		US-			
		US-			

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[illegible]

Examiner
Signature

HUNG VU

Date:

Considered

02/07/06

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Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Application Number	w/603,436
(use as many sheets as necessary)		Filing Date	06-23-03
Sheet 2 of 3		First Named Inventor	Sheng Teng Hsu
		Group/Art Unit	2891
		Examiner Name	H V
		Attorney Docket Number	SLA0733

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published	T2
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V		Y-K. CHOI, N. LINDERT, P. XUAN, S. TANG, D. HA, E. ANDERSON, T-J. KING, J. BOKOR, C. HU, <i>Sub-20 nm CMOS finFET technologies</i> , IEDM Tech. Dig., 2001.	

Examiner Signature: HUNG VU	Date: 02/07/06 Considered
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